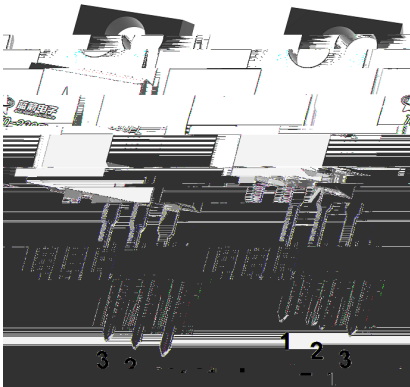
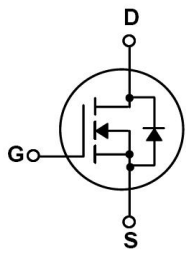


TO-220FL N MOS N-CHANNEL MOSFET in a TO-220FL Plastic Package.

Low gate charge, low crss, fast switching.

DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.



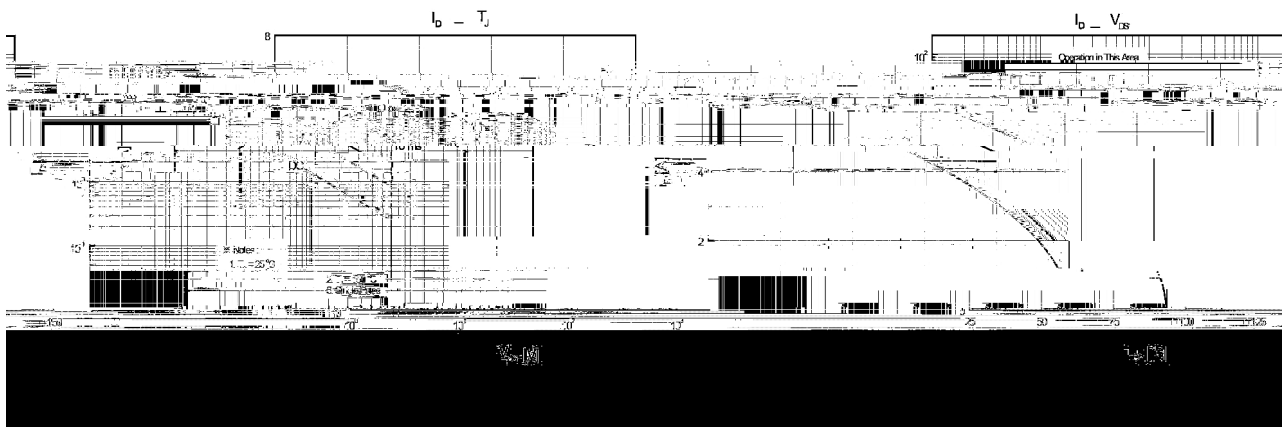
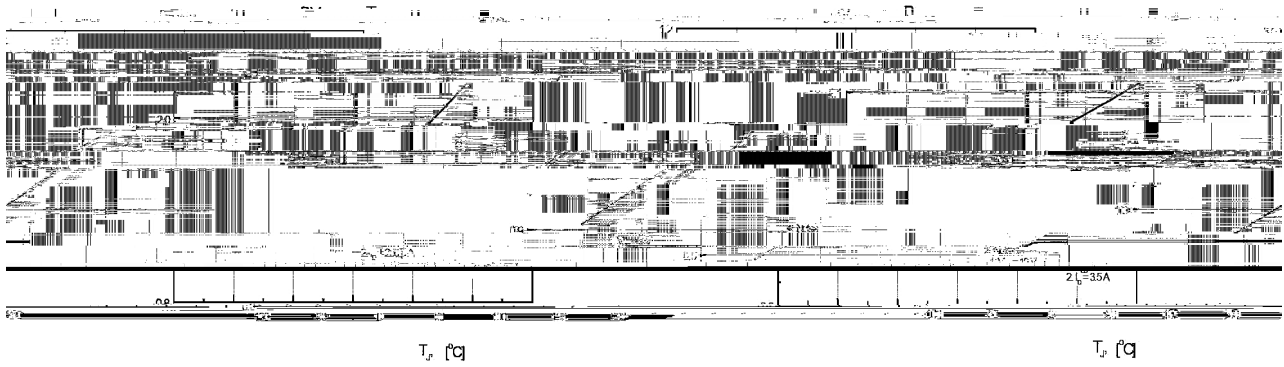
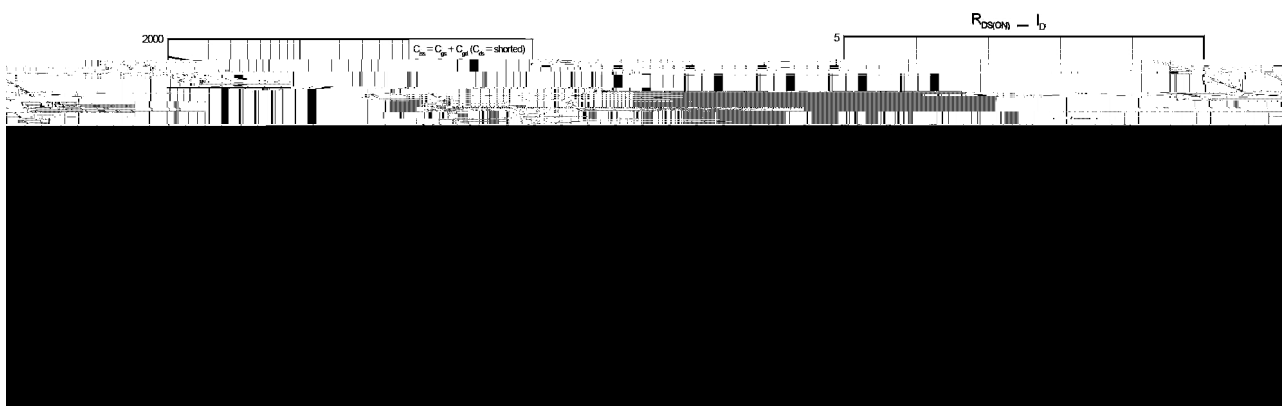
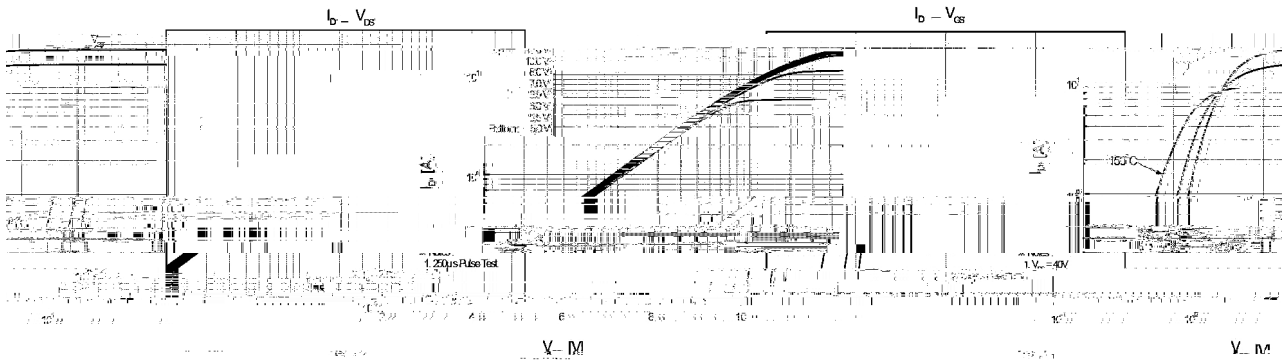
PIN 1 G PIN 2 D PIN 3 S

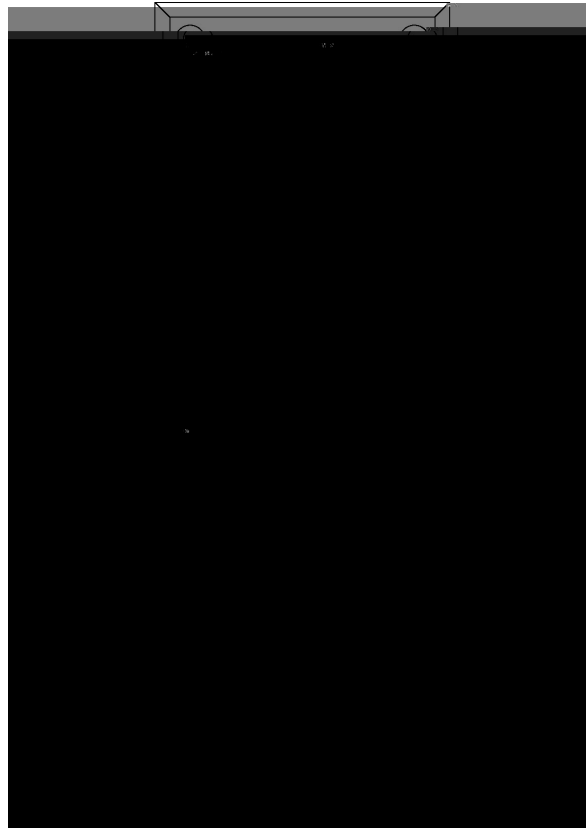
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	650	V
Drain Current	$I_D(T_C=25)$	7.0	A
Drain Current	$I_D(T_C=100)$	4.4	A
Drain Current - Pulsed	I_{DM}	28	A
Gate-Source Voltage	V_{GSS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	420	mJ
Repetitive Avalanche Energy	E_{AR}	14.7	mJ
Avalanche Current	I_{AR}	7.0	A
Power Dissipation	$P_D(T_C=25)$	48	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	650			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=650V$ $V_{GS}=0V$			1.0	μA
		$V_{DS}=520V$ $T_C=125$			100	μA
Gate-Body Leakage Current, Forward	I_{GSS}	$V_{GS}=\pm 30V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2.0		4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=3.5A$		1.1	1.3	
Forward Transconductance	g_{FS}	$V_{DS}=40V$ $I_D=3.5A$		8.2		S
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=7.0A$			1.4	V
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		1100	1500	pF
Output Capacitance	C_{oss}			110	150	pF
Reverse Transfer Capacitance	C_{rss}			12	16	pF
Total Gate Charge	Q_g	$I_D = 7.0A$ $V_{DS} = 520V$ $V_{GS} = 10V$		28		nC
Gate-to-Source Charge	Q_{gs}			7		nC
Gate-to-Drain Charge	Q_{gd}			12		nC
Turn-On Delay Time	$t_{d(on)}$					

 $V=7.78$ 0 0 10.5 291.12 422.0607 T $.475215$ $T_c1.2671$ $T_w(=3ain-So)$





BR

7N65

Note:

BR: Company Code

7N65: Product Type Code

****: Lot No. Code, code change with Lot No

